TCAD analysis of leakage current and breakdown voltage in small pitch 3D pixel sensors

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1. Introduction

50 x 50 - 1E 25 x 100 - 1E Α в Bump ATLAS ITk specifications: bad Bump Radiation tolerance up to $2*10^{16}n_{ed}/cm^2$; pad 100 µm *Operation voltage* $V_{op} < 250$ *V*; *Power dissipation* $< 10 \text{ mW/cm}^2$; n⁺ col p⁺ col. p⁺ col. *Hit efficiency* > 97%. n⁺ col. 50 µm metal bump passivation **Column Diameter** oxide ~ 5 µm -----p⁺ column **Active thickness** p-spray Gap $100 - 150 \mu m$ ~ 20 µm p⁻ high Ωcm sensor wafer n⁺ column p⁺⁺ low Ωcm handle wafer Handle wafer Thickness Metal to be deposited after thinning ~ 500 µm **Residual Handle** Wafer Thickness Handle wafer to be thinned 50 – 100 µm

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Smaller inter-electrode distance translates into:

- lower event pile up; ٠
- stronger radiation hardness. ٠

Geometrical parameters of small-pitch 3D detectors:

- active thickness 150 µm; •
- nominal radius ~2.5 µm; ٠
- effective gap ~20 µm. ٠

1. Introduction

Beam Test Results:

- At $10^{16} n_{eq}/cm^2$ a hit efficiency of 96% reached below 100V with perpendicular beam incidence;
- Larger voltages (~150 V) required at $1.8 \times 10^{16} n_{eq}/cm^2$.

Problem:

- Breakdown voltage not large enough compared with the required voltage for the worst cases;
- Power dissipation.

Objective:

- Locate the origin of the breakdown;
- Improve the breakdown voltage from geometry point of view.

Model Used	Temp
Perugia Surface Damage Model	-25 ℃
Perugia Bulk Damage Model	-25 ℃
CERN Bulk Damage Model	-38 ℃

TCAD Simulation



2. Simulation of Existing Detectors



 $k(I,V) = \frac{\Delta I}{\Delta V} \cdot \frac{V}{I}, k_{bd} \ge 4$

2. Simulation of Existing Detectors



I-V simulation based on Perugia Surface Model

Simulation in agreement with experiment (breakdown voltage ~130V).

Always breaks down at the Tip regardless of the bulk damage model used or the structure.

Simulation based on the CERN Bulk Damage Model used Temp=-38 °C, the leakage current was then scaled to -25 °C using the SRH model. Fluence=1E16, Normalized 2.00 40V 08V 1.75 --- Exp1, V_{Bd}=17N --- Exp2, V_{Bd}=172V



Comparison between simulation & experiments Calculated Damage Rate at V_{h} =100V, T=20°C

Irradiation	Fluence (n _{eq} /cm ²)	Structure	α [*] Experiment (10 ⁻¹⁷ A/cm)	α [*] Perugia Model (10 ⁻¹⁷ A/cm)	α [*] CERN Model (10 ⁻¹⁷ A/cm)
Neutron	1.0×10^{16}	50×50-1E	6.92 ± 1.14	5.54	4.87
		25×100-1E	4.25±0.91	6.69	4.22

Always breaks down at the Tip regardless of the bulk damage model used or the structure.

2. Simulation of Existing Detectors



Comparison between simulation & experiments

Calculated Damage Rate at V_b =100V, T=20°C

Irradiation	Fluence (n _{eq} /cm ²)	Structure	α [*] Experiment (10 ⁻¹⁷ A/cm)	α [*] Perugia Model (10 ⁻¹⁷ A/cm)	α [*] CERN Model (10 ⁻¹⁷ A/cm)
Neutron	1.5×10^{16}	50×50-1E	7.79 ± 2.53	10.74	7.65
		25×100-1E	3.87 ± 0.43	9.25	6.13

2. Simulation of Existing Detectors

Perugia Model:

- predicted breakdown voltage of both layouts before and after surface damage;
- the prediction of breakdown voltage is still in good agreement with experiment after bulk damage;
- the shape of the leakage current is different from the measured I-V curve.

CERN Model:

- leakage current well predicted at low reverse bias when the fluence is low;
- leakage current starts to deviate from measured results at high fluence;
- over-estimates the breakdown voltage for all simulated scenarios, including different layouts and fluences.



Conclusion:

- Breakdown voltage increases with the Radius and the Gap;
- Always breaks down at the Tip, contribution from the surface gets more and more important;
- The Radius & the Gap effect saturates.

Conclusion:

- Always breaks down at the Tip;
- Same breakdown voltage for both Doses due to long distance of the Tip from the surface;

20

22

Gap (µm)

Dose=10&20Mrad

Structure

Model

Used

26

24

• Breakdown voltage increases with the Radius & the Gap.

50×50-1E

Perugia Surface

Damage Model

28

30



Conclusion:

1): Breakdown voltage increases with the Radius;
2): The Radius & the Gap effect saturates.



Conclusion:

1): Breakdowns at the Tip after surface damage, thus same breakdown voltage for both Doses;

2): Breakdown voltage increases with the Radius & the Gap.



Difference in the breakdown voltage with/without Oxide is negligible; The trend applies for the CERN Model as well.

Safe to use only the bulk for breakdown prediction after radiation damage to boost the simulation.

Breakdown simulation With/Without Oxide





Conclusion:

1): Higher Fluence leads to higher breakdown voltage;

2): Breakdown voltage increases with the Radius & the Gap;

3): The Radius & the Gap effect saturates.





Conclusion:

1): Higher Fluence leads to higher breakdown voltage;

2): Breakdown voltage increases with the Radius & the Gap;

3): The Radius & the Gap effect saturates.

4. Summary

- The Tip limits the breakdown voltage, especially after radiation damage;
- 25 ×100-1E has higher breakdown voltage due to larger inter-electrode distance;
- Perugia Bulk Damage Model can predict the breakdown quite accurately, CERN Bulk Damage Model is better at predicting the leakage current;
- It is possible to increase the breakdown voltage of both designs by increasing the Radius/Gap, but the Radius & the Gap effect saturates.



Backup – **Pre-irradiation**



Back – Surface Damage



Backup - Power dissipation

• At the voltages of interest for a high hit efficiency, the power dissipation is still low

S. Terzo et al., Frontiers in Physics 9:624668



Back – Efficiency of irradiated modules at beam test

- RD53A assemblies with different 3D sensor geometries
- At $10^{16} n_{ed}/cm^2$ a hit efficiency of 96% at normal beam incidence reached below 100 V
- Larger voltages (~150 V) required at $1.8 \times 10^{16} n_{eq}/cm^2$



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